

Noritaka Usami

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#	Paper	IF	Citations
513	A quantum-dot spin qubit with coherence limited by charge noise and fidelity higher than 99.9. <i>Nature Nanotechnology</i> , 2018 , 13, 102-106	28.7	340
512	Optical properties of ZnO rods formed by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2003 , 83, 1635-1637	3.4	293
511	Island formation during growth of Ge on Si(100): A study using photoluminescence spectroscopy. <i>Applied Physics Letters</i> , 1995 , 66, 3024-3026	3.4	241
510	Formation of highly aligned ZnO tubes on sapphire (0001) substrates. <i>Applied Physics Letters</i> , 2004 , 84, 4098-4100	3.4	165
509	Growth of structure-controlled polycrystalline silicon ingots for solar cells by casting. <i>Acta Materialia</i> , 2006 , 54, 3191-3197	8.4	143
508	Control of Ge dots in dimension and position by selective epitaxial growth and their optical properties. <i>Applied Physics Letters</i> , 1998 , 72, 1617-1619	3.4	118
507	Growth of ZnO/MgZnO quantum wells on sapphire substrates and observation of the two-dimensional confinement effect. <i>Applied Physics Letters</i> , 2005 , 86, 032105	3.4	109
506	Investigation of grain boundaries in BaSi ₂ epitaxial films on Si(1 1 1) substrates using transmission electron microscopy and electron-beam-induced current technique. <i>Journal of Crystal Growth</i> , 2012 , 348, 75-79	1.6	108
505	Effects of growth temperature on the characteristics of ZnO epitaxial films deposited by metalorganic chemical vapor deposition. <i>Thin Solid Films</i> , 2004 , 449, 12-19	2.2	104
504	Directional growth method to obtain high quality polycrystalline silicon from its melt. <i>Journal of Crystal Growth</i> , 2006 , 292, 282-285	1.6	90
503	In situ observation of elementary growth steps on the surface of protein crystals by laser confocal microscopy. <i>Journal of Crystal Growth</i> , 2004 , 262, 536-542	1.6	89
502	Grain growth behaviors of polycrystalline silicon during melt growth processes. <i>Journal of Crystal Growth</i> , 2004 , 266, 441-448	1.6	89
501	Low-temperature (180 °C) formation of large-grained Ge (111) thin film on insulator using accelerated metal-induced crystallization. <i>Applied Physics Letters</i> , 2014 , 104, 022106	3.4	88
500	Enhanced quantum efficiency of solar cells with self-assembled Ge dots stacked in multilayer structure. <i>Applied Physics Letters</i> , 2003 , 83, 1258-1260	3.4	86
499	Generation mechanism of dislocations during directional solidification of multicrystalline silicon using artificially designed seed. <i>Journal of Crystal Growth</i> , 2010 , 312, 897-901	1.6	84
498	Highly (111)-oriented Ge thin films on insulators formed by Al-induced crystallization. <i>Applied Physics Letters</i> , 2012 , 101, 072106	3.4	78
497	Investigation of the recombination mechanism of excess carriers in undoped BaSi ₂ films on silicon. <i>Journal of Applied Physics</i> , 2012 , 112, 083108	2.5	75

496	In situ observation of Si faceted dendrite growth from low-degree-of-undercooling melts. <i>Acta Materialia</i> , 2008 , 56, 2663-2668	8.4	74
495	Exploring the potential of semiconducting BaSi ₂ for thin-film solar cell applications. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 023001	3	69
494	Formation mechanism of parallel twins related to Si-faceted dendrite growth. <i>Scripta Materialia</i> , 2007 , 57, 81-84	5.6	68
493	Influence of grain size and surface condition on minority-carrier lifetime in undoped n-BaSi ₂ on Si(111). <i>Journal of Applied Physics</i> , 2014 , 115, 193510	2.5	64
492	In situ observations of crystal growth behavior of silicon melt. <i>Journal of Crystal Growth</i> , 2002 , 243, 275-282	3.8	64
491	Optical anisotropy in wire-geometry SiGe layers grown by gas-source selective epitaxial growth technique. <i>Applied Physics Letters</i> , 1994 , 64, 1126-1128	3.4	63
490	Strong resonant luminescence from Ge quantum dots in photonic crystal microcavity at room temperature. <i>Applied Physics Letters</i> , 2006 , 89, 201102	3.4	62
489	p-BaSi ₂ /n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. <i>Applied Physics Letters</i> , 2016 , 108, 152101	3.4	62
488	Growth mechanism of Si-faceted dendrites. <i>Physical Review Letters</i> , 2008 , 101, 055503	7.4	61
487	In-situ heavily p-type doping of over 10 ²⁰ cm ⁻³ in semiconducting BaSi ₂ thin films for solar cells applications. <i>Applied Physics Letters</i> , 2013 , 102, 112107	3.4	59
486	In-situ observations of melt growth behavior of polycrystalline silicon. <i>Journal of Crystal Growth</i> , 2004 , 262, 124-129	1.6	59
485	Determination of Bulk Minority-Carrier Lifetime in BaSi ₂ Earth-Abundant Absorber Films by Utilizing a Drastic Enhancement of Carrier Lifetime by Post-Growth Annealing. <i>Applied Physics Express</i> , 2013 , 6, 112302	2.4	58
484	Investigation of the open-circuit voltage in solar cells doped with quantum dots. <i>Scientific Reports</i> , 2013 , 3, 2703	4.9	56
483	In-plane strain fluctuation in strained-Si/SiGe heterostructures. <i>Applied Physics Letters</i> , 2003 , 83, 4339-4341	3.4	56
482	Molecular beam epitaxy of BaSi ₂ thin films on Si(001) substrates. <i>Journal of Crystal Growth</i> , 2012 , 345, 16-21	1.6	53
481	Photoresponse Properties of Polycrystalline BaSi ₂ Films Grown on SiO ₂ Substrates Using (111)-Oriented Si Layers by an Aluminum-Induced Crystallization Method. <i>Applied Physics Express</i> , 2009 , 2, 051601	2.4	52
480	Abrupt Si/Ge interface formation using atomic hydrogen in Si molecular beam epitaxy. <i>Applied Physics Letters</i> , 1994 , 65, 2975-2977	3.4	50
479	Pressure-Dependent ZnO Nanocrystal Growth in a Chemical Vapor Deposition Process. <i>Journal of Physical Chemistry B</i> , 2004 , 108, 10899-10902	3.4	48

478	Room-temperature electroluminescence from Si microdisks with Ge quantum dots. <i>Optics Express</i> , 2010 , 18, 13945-50	3.3	46
477	Growth of SiGe bulk crystal with uniform composition by directly controlling the growth temperature at the crystal-melt interface using in situ monitoring system. <i>Journal of Crystal Growth</i> , 2001 , 224, 204-211	1.6	46
476	Low-temperature growth of ZnO nanostructure networks. <i>Journal of Applied Physics</i> , 2004 , 96, 340-343	2.5	45
475	Realization of crescent-shaped SiGe quantum wire structures on a V-groove patterned Si substrate by gas-source Si molecular beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 2789-2791	3.4	45
474	Observation of deep-level-free band edge luminescence and quantum confinement in strained Si _{1-x} Ge _x /Si single quantum well structures grown by solid source Si molecular beam epitaxy. <i>Applied Physics Letters</i> , 1992 , 61, 1706-1708	3.4	45
473	Orientation Control of Large-Grained Si Films on Insulators by Thickness-Modulated Al-Induced Crystallization. <i>Crystal Growth and Design</i> , 2013 , 13, 1767-1770	3.5	43
472	Formation mechanism of a faceted interface: In situ observation of the Si(100) crystal-melt interface during crystal growth. <i>Physical Review B</i> , 2009 , 80,	3.3	43
471	Improved photoresponsivity of semiconducting BaSi ₂ epitaxial films grown on a tunnel junction for thin-film solar cells. <i>Applied Physics Letters</i> , 2012 , 100, 152114	3.4	42
470	Fabrication of high-quality strain-relaxed thin SiGe layers on ion-implanted Si substrates. <i>Applied Physics Letters</i> , 2004 , 85, 2514-2516	3.4	42
469	Luminescence study on interdiffusion in strained Si _{1-x} Ge _x /Si single quantum wells grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 1651-1653	3.4	42
468	Analysis of the electrical properties of Cr/n-BaSi ₂ Schottky junction and n-BaSi ₂ /p-Si heterojunction diodes for solar cell applications. <i>Journal of Applied Physics</i> , 2014 , 115, 223701	2.5	41
467	Control of Grain Boundary Propagation in Mono-Like Si: Utilization of Functional Grain Boundaries. <i>Applied Physics Express</i> , 2013 , 6, 025505	2.4	41
466	Relationship between grain boundary structures in Si multicrystals and generation of dislocations during crystal growth. <i>Journal of Applied Physics</i> , 2010 , 107, 013511	2.5	41
465	Temperature dependence of microscopic photoluminescence spectra of quantum dots and quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998 , 2, 573-577	3	41
464	Photoluminescence investigation on growth mode changeover of Ge on Si(100). <i>Journal of Crystal Growth</i> , 1995 , 157, 265-269	1.6	41
463	Enhancement of radiative recombination in Si-based quantum wells with neighboring confinement structure. <i>Applied Physics Letters</i> , 1995 , 67, 524-526	3.4	41
462	Dislocation glide motion in heteroepitaxial thin films of Si _{1-x} Ge _x /Si(100). <i>Philosophical Magazine Letters</i> , 1993 , 67, 165-171	1	41
461	Observation of lateral confinement effect in Ge quantum wires self-aligned at step edges on Si(100). <i>Applied Physics Letters</i> , 1996 , 68, 1847-1849	3.4	40

460	Gas-source molecular beam epitaxy and luminescence characterization of strained Si _{1-x} Gex/Si quantum wells. <i>Journal of Crystal Growth</i> , 1994 , 136, 315-321	1.6	39
459	Configuration and local elastic interaction of ferroelectric domains and misfit dislocation in PbTiO ₃ /SrTiO ₃ epitaxial thin films. <i>Science and Technology of Advanced Materials</i> , 2011 , 12, 034413	7.1	37
458	Silicon-based light emitters fabricated by embedding Ge self-assembled quantum dots in microdisks. <i>Applied Physics Letters</i> , 2007 , 91, 011104	3.4	37
457	Mono-Like Silicon Growth Using Functional Grain Boundaries to Limit Area of Multicrystalline Grains. <i>IEEE Journal of Photovoltaics</i> , 2014 , 4, 84-87	3.7	36
456	Selective formation of large-grained, (100)- or (111)-oriented Si on glass by Al-induced layer exchange. <i>Journal of Applied Physics</i> , 2014 , 115, 094301	2.5	36
455	Growth of multicrystalline Si ingots using noncontact crucible method for reduction of stress. <i>Journal of Crystal Growth</i> , 2012 , 344, 6-11	1.6	35
454	Luminescence from Strained Si _{1-x} Gex/Si Quantum Wells Grown by Si Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 1502-1507	1.4	35
453	Enhanced carrier extraction from Ge quantum dots in Si solar cells under strong photoexcitation. <i>Applied Physics Letters</i> , 2012 , 101, 133905	3.4	34
452	Floating cast method to realize high-quality Si bulk multicrystals for solar cells. <i>Journal of Crystal Growth</i> , 2009 , 311, 228-231	1.6	34
451	Microstructures of Si multicrystals and their impact on minority carrier diffusion length. <i>Acta Materialia</i> , 2009 , 57, 3268-3276	8.4	34
450	Epitaxial Growth and Polarity of ZnO Films on Sapphire (0001) Substrates by Low-Pressure Metal Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 2291-2295	1.4	34
449	Seed manipulation for artificially controlled defect technique in new growth method for quasi-monocrystalline Si ingot based on casting. <i>Applied Physics Express</i> , 2015 , 8, 105501	2.4	33
448	Realization of single-phase BaSi ₂ films by vacuum evaporation with suitable optical properties and carrier lifetime for solar cell applications. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 07JE02	1.4	32
447	Compositional variation in Si-rich SiGe single crystals grown by multi-component zone melting method using Si seed and source crystals. <i>Journal of Crystal Growth</i> , 2002 , 240, 373-381	1.6	32
446	Electroluminescence from Strained SiGe/Si Quantum Well Structures Grown by Solid Source Si Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1992 , 31, L1015-L1017	1.4	31
445	Fabrication and characterization of BaSi ₂ epitaxial films over 1 μm in thickness on Si(111). <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04ER04	1.4	29
444	On the Controlling Mechanism of Preferential Orientation of Polycrystalline-Silicon Thin Films Grown by Aluminum-Induced Crystallization. <i>Applied Physics Express</i> , 2010 , 3, 095803	2.4	29
443	Fabrication of (111)-oriented Si layers on SiO ₂ substrates by an aluminum-induced crystallization method and subsequent growth of semiconducting BaSi ₂ layers for photovoltaic application. <i>Journal of Crystal Growth</i> , 2009 , 311, 3581-3586	1.6	29

442	Band-edge photoluminescence of SiGe/strained-Si/SiGe type-II quantum wells on Si(100). <i>Applied Physics Letters</i> , 1993 , 63, 3509-3511	3.4	29
441	High-temperature operation of strained Si _{0.65} Ge _{0.35} /Si(111) p-type multiple-quantum-well light-emitting diode grown by solid source Si molecular-beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 967-969	3.4	29
440	Quantum Size Effect of Excitonic Band-Edge Luminescence in Strained Si _{1-x} Ge _x /Si Single Quantum Well Structures Grown by Gas-Source Si Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1992 , 31, L1319-L1321	1.4	29
439	Simultaneous enhanced photon capture and carrier generation in Si solar cells using Ge quantum dot photonic nanocrystals. <i>Nanotechnology</i> , 2012 , 23, 185401	3.4	28
438	Fabrication of n+-BaSi ₂ /p+-Si Tunnel Junction on Si(111) Surface by Molecular Beam Epitaxy for Photovoltaic Applications. <i>Applied Physics Express</i> , 2010 , 3, 021301	2.4	28
437	Ge composition dependence of properties of solar cells based on multicrystalline SiGe with microscopic compositional distribution. <i>Journal of Applied Physics</i> , 2004 , 96, 1238-1241	2.5	28
436	Structural and electrical characterizations of crack-free BaSi ₂ thin films fabricated by thermal evaporation. <i>Thin Solid Films</i> , 2015 , 595, 68-72	2.2	27
435	Precipitation control and activation enhancement in boron-doped p+-BaSi ₂ films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2014 , 104, 252104	3.4	27
434	High-Quality Polycrystalline Silicon Films with Minority Carrier Lifetimes over 5 μ s Formed by Flash Lamp Annealing of Precursor Amorphous Silicon Films Prepared by Catalytic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 7198-7203	1.4	27
433	Growth of SiGe bulk crystals with uniform composition by utilizing feedback control system of the crystal-melt interface position for precise control of the growth temperature. <i>Journal of Crystal Growth</i> , 2003 , 250, 298-304	1.6	27
432	Abrupt compositional transition in luminescent Si _{1-x} Ge _x /Si quantum well structures fabricated by segregant assisted growth using Sb adlayer. <i>Applied Physics Letters</i> , 1993 , 63, 388-390	3.4	27
431	Evaluation of potential variations around grain boundaries in BaSi ₂ epitaxial films by Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2013 , 103, 142113	3.4	26
430	Growth of multicrystalline Si with controlled grain boundary configuration by the floating zone technique. <i>Journal of Crystal Growth</i> , 2005 , 280, 419-424	1.6	26
429	Effects of deposition rate on the structure and electron density of evaporated BaSi ₂ films. <i>Journal of Applied Physics</i> , 2016 , 120, 045103	2.5	26
428	Raman scattering and x-ray absorption studies of Ge β i nanocrystallization. <i>Applied Physics Letters</i> , 2002 , 80, 488-490	3.4	25
427	Selective epitaxial growth of dot structures on patterned Si substrates by gas source molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 1999 , 14, 257-265	1.8	25
426	Role of heterointerface on enhancement of no-phonon luminescence in Si-based neighboring confinement structure. <i>Applied Physics Letters</i> , 1996 , 68, 2340-2342	3.4	25
425	Formation of metastable cubic phase in SnS thin films fabricated by thermal evaporation. <i>Thin Solid Films</i> , 2017 , 639, 7-11	2.2	24

424	Fabrication of single-phase polycrystalline BaSi ₂ thin films on silicon substrates by vacuum evaporation for solar cell applications. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KC03	1.4	24
423	Quantitative analysis of subgrain boundaries in Si multicrystals and their impact on electrical properties and solar cell performance. <i>Journal of Applied Physics</i> , 2009 , 105, 044909	2.5	24
422	N-type doping of BaSi ₂ epitaxial films by phosphorus ion implantation and thermal annealing. <i>Thin Solid Films</i> , 2014 , 557, 90-93	2.2	23
421	Crystal quality of a 6H-SiC layer grown over macrodefects by liquid-phase epitaxy: a Raman spectroscopic study. <i>Thin Solid Films</i> , 2005 , 476, 206-209	2.2	23
420	Growth mechanism of the Si <110> faceted dendrite. <i>Physical Review B</i> , 2010 , 81,	3.3	22
419	Formation mechanism of twin boundaries during crystal growth of silicon. <i>Scripta Materialia</i> , 2011 , 65, 556-559	5.6	21
418	Floating zone growth of Si-rich SiGe bulk crystal using pre-synthesized SiGe feed rod with uniform composition. <i>Journal of Crystal Growth</i> , 2005 , 284, 57-64	1.6	21
417	Potential variations around grain boundaries in impurity-doped BaSi ₂ epitaxial films evaluated by Kelvin probe force microscopy. <i>Journal of Applied Physics</i> , 2014 , 116, 123709	2.5	20
416	N-type doping of BaSi ₂ epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. <i>Thin Solid Films</i> , 2014 , 567, 105-108	2.2	20
415	Silicon-Based Light-Emitting Devices Based on Ge Self-Assembled Quantum Dots Embedded in Optical Cavities. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2012 , 18, 1830-1838	3.8	20
414	Impact of type of crystal defects in multicrystalline Si on electrical properties and interaction with impurities. <i>Journal of Applied Physics</i> , 2011 , 109, 033504	2.5	20
413	Strain dependence of hole effective mass and scattering mechanism in strained Ge channel structures. <i>Applied Physics Letters</i> , 2009 , 95, 122109	3.4	20
412	Epitaxial relation and island growth of perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(1 1 1) substrate. <i>Journal of Crystal Growth</i> , 2004 , 262, 196-201	1.6	20
411	Drastic modification of the growth mode of Ge quantum dots on Si by using boron adlayer. <i>Thin Solid Films</i> , 2000 , 369, 84-87	2.2	20
410	On the Mechanism of BaSi ₂ Thin Film Formation on Si Substrate by Vacuum Evaporation. <i>Procedia Engineering</i> , 2016 , 141, 23-26		19
409	Simple method for significant improvement of minority-carrier lifetime of evaporated BaSi ₂ thin film by sputtered-AlO _x passivation. <i>Materials Science in Semiconductor Processing</i> , 2018 , 76, 37-41	4.3	19
408	Lattice and grain-boundary diffusions of boron atoms in BaSi ₂ epitaxial films on Si(111). <i>Journal of Applied Physics</i> , 2013 , 113, 053511	2.5	19
407	Dependence of crystal orientation in Al-induced crystallized poly-Si layers on SiO ₂ insertion layer thickness. <i>Journal of Crystal Growth</i> , 2012 , 356, 65-69	1.6	19

406	On the origin of strain fluctuation in strained-Si grown on SiGe-on-insulator and SiGe virtual substrates. <i>Applied Physics Letters</i> , 2004 , 85, 1335-1337	3.4	19
405	Effects of high pressure on the growth kinetics of orthorhombic lysozyme crystals. <i>Journal of Crystal Growth</i> , 2003 , 254, 188-195	1.6	19
404	Effects of crystal defects and their interactions with impurities on electrical properties of multicrystalline Si. <i>Journal of Applied Physics</i> , 2013 , 113, 133503	2.5	18
403	Generation mechanism of dislocations and their clusters in multicrystalline silicon during two-dimensional growth. <i>Journal of Applied Physics</i> , 2011 , 110, 083530	2.5	18
402	Implementation of faceted dendrite growth on floating cast method to realize high-quality multicrystalline Si ingot for solar cells. <i>Journal of Applied Physics</i> , 2011 , 109, 083527	2.5	18
401	Upper limit of two-dimensional hole gas mobility in strained Ge/SiGe heterostructures. <i>Applied Physics Letters</i> , 2012 , 100, 222102	3.4	18
400	Determination of lattice parameters of SiGe/Si(110) heterostructures. <i>Thin Solid Films</i> , 2006 , 508, 132-135	2.2	18
399	Influence of the elastic strain on the band structure of ellipsoidal SiGe coherently embedded in the Si matrix. <i>Journal of Applied Physics</i> , 2003 , 94, 916-920	2.5	18
398	Growth and characterization of ⁷⁰ Ge/ ⁷⁴ Ge isotope superlattices. <i>Thin Solid Films</i> , 2000 , 369, 405-408	2.2	18
397	Is low temperature growth the solution to abrupt Si/Si _{1-x} Ge _x interface formation?. <i>Journal of Crystal Growth</i> , 1993 , 127, 401-405	1.6	18
396	Silicon-germanium (SiGe) nanostructures 2011 ,		18
395	Photoresponse properties of BaSi ₂ film grown on Si (100) by vacuum evaporation. <i>Materials Research Express</i> , 2016 , 3, 076204	1.7	17
394	Simple Vacuum Evaporation Route to BaSi ₂ Thin Films for Solar Cell Applications. <i>Procedia Engineering</i> , 2016 , 141, 27-31		17
393	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. <i>CrystEngComm</i> , 2014 , 16, 2578	3.3	17
392	Formation process of Si ₃ N ₄ particles on surface of Si ingots grown using silica crucibles with Si ₃ N ₄ coating by noncontact crucible method. <i>Journal of Crystal Growth</i> , 2014 , 389, 112-119	1.6	17
391	Modification of Local Structure and Its Influence on Electrical Activity of Near (310) Σ ₅ Grain Boundary in Bulk Silicon. <i>Materials Transactions</i> , 2007 , 48, 143-147	1.3	17
390	Effects of spacer thickness on quantum efficiency of the solar cells with embedded Ge islands in the intrinsic layer. <i>Applied Physics Letters</i> , 2004 , 84, 2802-2804	3.4	17
389	Formation and optical properties of SiGe/Si quantum structures. <i>Applied Surface Science</i> , 1996 , 102, 263-271	2.7	17

388	Systematic blue shift of exciton luminescence in strained Si _{1-x} Ge _x /Si quantum well structures grown by gas source silicon molecular beam epitaxy. <i>Thin Solid Films</i> , 1992 , 222, 1-4	2.2	17
387	Evaluation of minority carrier diffusion length of undoped n-BaSi ₂ epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 078004	1.4	16
386	Effects of formation of mini-bands in two-dimensional array of silicon nanodisks with SiC interlayer for quantum dot solar cells. <i>Nanotechnology</i> , 2013 , 24, 015301	3.4	16
385	Postannealing effects on undoped BaSi ₂ evaporated films grown on Si substrates. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DB05	1.4	16
384	Double-Layered Ge Thin Films on Insulators Formed by an Al-Induced Layer-Exchange Process. <i>Crystal Growth and Design</i> , 2013 , 13, 3908-3912	3.5	16
383	Large-Grained Polycrystalline (111) Ge Films on Insulators by Thickness-Controlled Al-Induced Crystallization. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, Q195-Q199	2	16
382	Influence of structural imperfection of β grain boundaries in bulk multicrystalline Si on their electrical activities. <i>Journal of Applied Physics</i> , 2007 , 101, 063509	2.5	16
381	Magnetotransport properties of Ge channels with extremely high compressive strain. <i>Applied Physics Letters</i> , 2006 , 89, 162103	3.4	16
380	Strain-driven alloying: effect on sizes, shape and photoluminescence of GeSi/Si(001) self-assembled islands. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 89, 62-65	2.1	16
379	Physical model for the evaluation of solid-liquid interfacial tension in silicon. <i>Journal of Applied Physics</i> , 2001 , 90, 750-755	2.5	16
378	Modification of the growth mode of Ge on Si by buried Ge islands. <i>Applied Physics Letters</i> , 2000 , 76, 3723-3725	3.4	16
377	Effects of the Si/Al layer thickness on the continuity, crystalline orientation and the growth kinetics of the poly-Si thin films formed by aluminum-induced crystallization. <i>Thin Solid Films</i> , 2016 , 616, 213-219	2.2	16
376	Formation of BaSi ₂ heterojunction solar cells using transparent MoO _x hole transport layers. <i>Applied Physics Letters</i> , 2015 , 106, 122104	3.4	15
375	Enhancement of light emission from Ge quantum dots by photonic crystal nanocavities at room-temperature. <i>Journal of Crystal Growth</i> , 2013 , 378, 636-639	1.6	15
374	Structural study on phosphorus doping of BaSi ₂ epitaxial films by ion implantation. <i>Thin Solid Films</i> , 2013 , 534, 470-473	2.2	15
373	Mechanism of strain relaxation in BaSi ₂ epitaxial films on Si(111) substrates during post-growth annealing and application for film exfoliation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1677-1680		15
372	Electrical properties of oxides grown on strained Si using microwave N ₂ O plasma. <i>Applied Physics Letters</i> , 1997 , 70, 66-68	3.4	15
371	Acceptorlike Behavior of Defects in SiGe Alloys Grown by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 4630-4633	1.4	15

370	Growth temperature dependence of lattice structures of SiGe/graded buffer structures grown on Si(110) substrates by gas-source MBE. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 343-348	1.6	15
369	Melt growth of multicrystalline SiGe with large compositional distribution for new solar cell applications. <i>Solar Energy Materials and Solar Cells</i> , 2002 , 72, 93-100	6.4	15
368	Growth and properties of SiGe multicrystals with microscopic compositional distribution for high-efficiency solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2002 , 73, 305-320	6.4	15
367	A simple approach to determine preferential growth orientation using multiple seed crystals with random orientations and its utilization for seed optimization to restrain polycrystallization of SiGe bulk crystal. <i>Journal of Crystal Growth</i> , 2005 , 276, 393-400	1.6	15
366	Marked enhancement of the photoresponsivity and minority-carrier lifetime of BaSi ₂ passivated with atomic hydrogen. <i>Physical Review Materials</i> , 2019 , 3,	3.2	15
365	Impact of silicon quantum dot super lattice and quantum well structure as intermediate layer on p-i-n silicon solar cells. <i>Progress in Photovoltaics: Research and Applications</i> , 2016 , 24, 774-780	6.8	15
364	Hydrogen concentration at a-Si:H/c-Si heterointerfaces—the impact of deposition temperature on passivation performance. <i>AIP Advances</i> , 2019 , 9, 075115	1.5	14
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